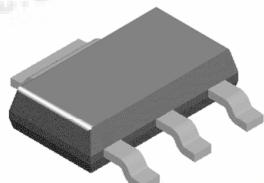




SB29003

High Voltage Transistor



1 SOT-223
Marking: 5463003
1. Base 2. Collector 3. Emitter

Absolute Maximum Ratings $T_a = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Value | Units |
|-----------|--|-----------|------------------|
| V_{CBO} | Collector-Base Voltage | 500 | V |
| V_{CEO} | Collector-Emitter Voltage | 400 | V |
| V_{EBO} | Emitter-Base Voltage | 6 | V |
| I_C | Collector Current | 300 | mA |
| P_C | Collector Dissipation ($T_C = 25^\circ\text{C}$) | 2 | W |
| T_J | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{STG} | Storage Temperature | -55 ~ 150 | $^\circ\text{C}$ |

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Conditions | Min. | Max | Units |
|---------------|--|--|----------------------|--------------------|---------------|
| BV_{CBO} | Collector-Base Breakdown Voltage | $I_C = 100\mu\text{A}, I_B = 0$ | 500 | | V |
| BV_{CER} | Collector-Emitter Breakdown Voltage * | $I_C = 1\text{mA}, I_B = 0$ | 400 | | V |
| BV_{EBO} | Emitter-Base Breakdown Voltage | $I_E = 100\mu\text{A}, I_C = 0$ | 6 | | V |
| I_{CBO} | Collector Cut-off Current | $V_{CB} = 400\text{V}, I_E = 0$ | | 0.1 | μA |
| I_{CES} | Collector Cut-off Current | $V_{CE} = 400\text{V}, I_B = 0$ | | 0.5 | μA |
| I_{EBO} | Emitter Cut-off Current | $V_{EB} = 4\text{V}, I_C = 0$ | | 0.1 | μA |
| h_{FE} | DC Current Gain * | $V_{CE} = 10\text{V}, I_C = 1\text{mA}$ $V_{CE} = 10\text{V}, I_C = 10\text{mA}$ $V_{CE} = 10\text{V}, I_C = 50\text{mA}$ $V_{CE} = 10\text{V}, I_C = 100\text{mA}$ | 40 50 45 40 | 200 | |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage * | $I_C = 1\text{mA}, I_B = 0.1\text{mA}$ $I_C = 10\text{mA}, I_B = 1\text{mA}$ $I_C = 50\text{mA}, I_B = 5\text{mA}$ | | 0.4 0.5 0.75 | V |
| $V_{BE(sat)}$ | Base-Emitter Saturation Voltage * | $I_C = 10\text{mA}, I_B = 1\text{mA}$ | | 0.75 | V |
| C_{ob} | Output Capacitance | $V_{CB} = 20\text{V}, I_E = 0, f = 1\text{MHz}$ | | 7 | pF |

* Pulse Test: PW $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

Typical Performance Characteristics

Figure 1. DC Current Gain

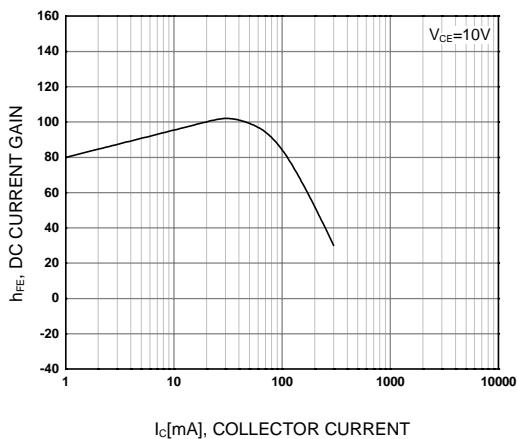


Figure 3. On Voltage

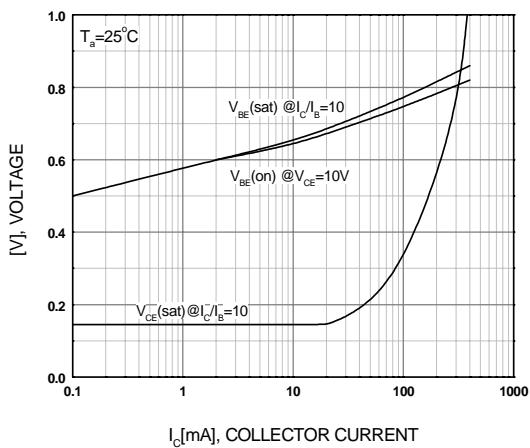


Figure 5. High Frequency Current Gain

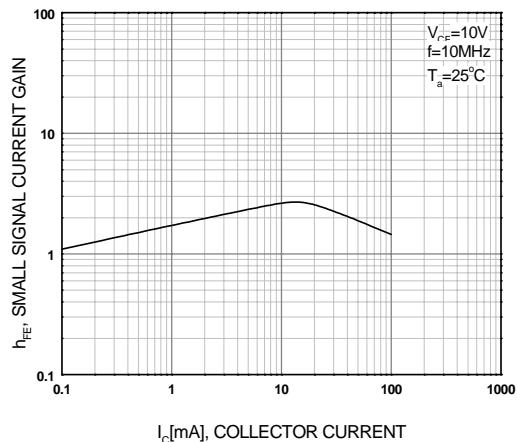


Figure 2. Capacitance

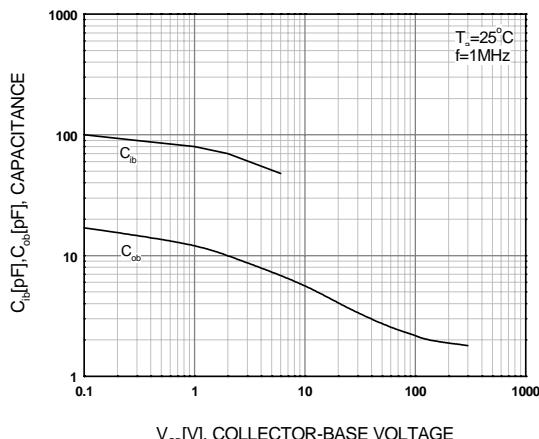
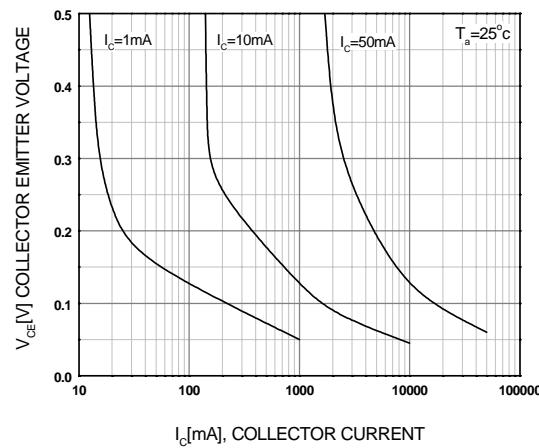
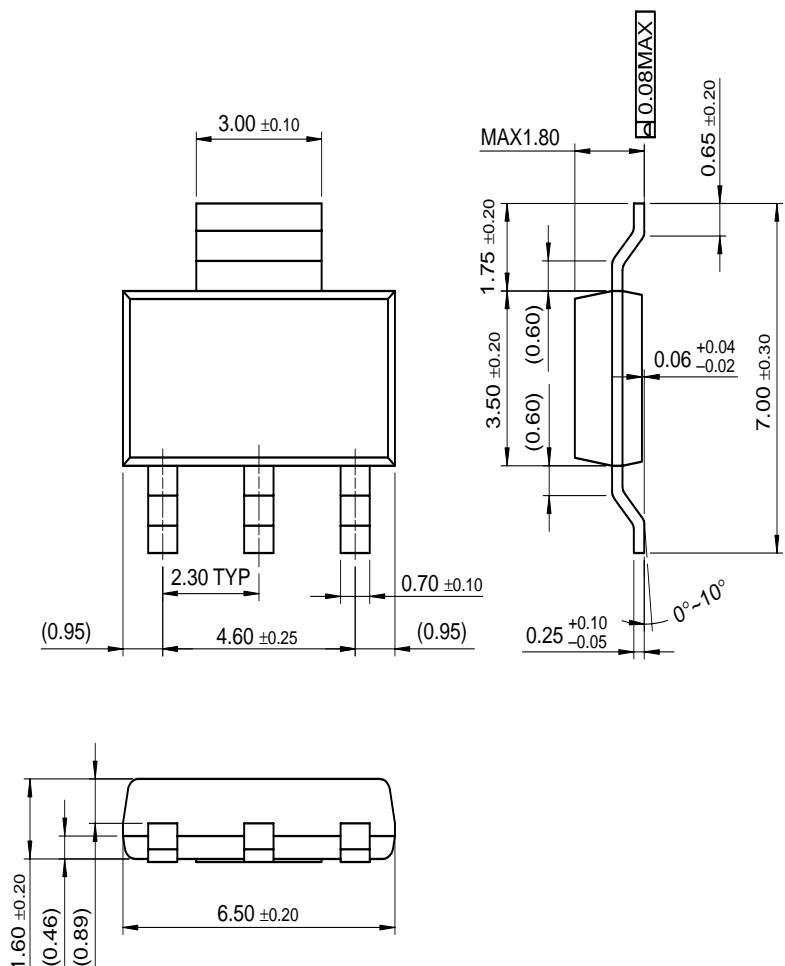


Figure 4. Collector Saturation Region



Mechanical Dimensions

SOT-223



Dimensions in Millimeters

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